

Inchange Semiconductor

Product Specification

Silicon NPN Power Transistors

BDX53/A/B/C

DESCRIPTION

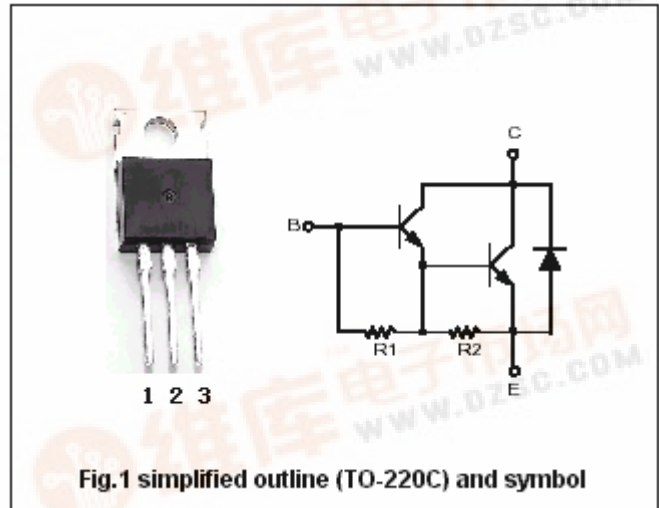
- With TO-220C package
- High DC current gain
- DARLINGTON
- Complement to type BDX54/A/B/C

APPLICATIONS

- Power linear and switching applications
- Hammer drivers, audio amplifiers

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter



Absolute maximum ratings(Ta=25)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT	
V _{CBO}	Collector-base voltage	Open emitter	BDX53	45	V
			BDX53A	60	
			BDX53B	80	
			BDX53C	100	
V _{CEO}	Collector-emitter voltage	Open base	BDX53	45	V
			BDX53A	60	
			BDX53B	80	
			BDX53C	100	
V _{EBO}	Emitter-base voltage	Open collector	5	V	
I _C	Collector current-DC		8	A	
I _{CM}	Collector current-Pulse		12	A	
I _B	Base current		0.2	A	
P _C	Collector power dissipation	T _C =25	60	W	
T _j	Junction temperature		150		
T _{stg}	Storage temperature		-65~150		

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
R _{th j-c}	Thermal resistance junction to case	2.08	/W



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CHARACTERISTICS

T_j=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEO(SUS)}	Collector-emitter sustaining voltage	BDX53	I _C =0.1A, I _B =0			V
		BDX53A				
		BDX53B				
		BDX53C				
V _{CEsat}	Collector-emitter saturation voltage	I _C =3A, I _B =12mA			2.0	V
V _{BE sat}	Base-emitter saturation voltage	I _C =3A, I _B =12mA			2.5	V
I _{CBO}	Collector cut-off current	BDX53			0.2	mA
		BDX53A				
		BDX53B				
		BDX53C				
I _{CEO}	Collector cut-off current	BDX53			0.5	mA
		BDX53A				
		BDX53B				
		BDX53C				
I _{EBO}	Emitter cut-off current	V _{EB} =5V; I _C =0			2.0	mA
h _{FE}	DC current gain	I _C =3A; V _{CE} =3V	750			
V _{F-1}	Forward diode voltage	I _F =3A		1.8	2.5	V
V _{F-2}	Forward diode voltage	I _F =8A		2.5		V

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PACKAGE OUTLINE

